

CIR-V4SESX2632G

DDR4 SO-DIMM 2666MHz 32GB with ECC

Description

This specification defines the electrical and mechanical requirements for 260 pin, 1.2 V (VDD), Double Data Rate, Synchronous DRAM Dual In-Line Memory Modules (DDR4 SDRAM ECC SO-DIMM). This DDR4 ECC SO-DIMMs is intended for use as main memory when installed in PCs, laptops and other systems.

Reference design examples are included which provide an initial basis for DDR4 ECC SO-DIMM designs. Modifications to these reference designs may be required to meet all system timing, signal integrity and thermal requirements for DDR4-2666 support.

All DDR4 ECC SO-DIMM implementations must use simulations and lab verification to ensure proper timing requirement and signal integrity in the design.

_	Specifications						
-	Density	32GB					
-	Pin Count	260pin					
	Туре	Unbuffered					
	Dimensions	69.73mm x 30.13mm					
	ECC	with ECC					
	Component Config	2G x 8 bit					
	Data Rate	2666MHz					
	CAS Latency	19 1.2V					
	Voltage						
	PCB Layers	8					
-	Operating Temp.(TCASE)	0°C~+85°C					
	Module Ranks	Dual Rank					

Features

- JEDEC Standard 260-pin Small-Outline Dual In-Line Memory Module
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15,16,17,18,19
- Inputs and Outputs are SSTL-12 compatible
- Low-Power auto self-refresh (LPASR)
- SDRAMs have 16 internal banks for concurrent operation (4 Bank Group of 4banks each)
- Normal and Dynamic On-Die Termination for data, strobe and mask signals.
- Data bus inversion (DBI) for data bus
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the MRS
- Selectable BC4 or BL8 on-the fly (OTF)
- ECC function support
- RoHS and Halogen free

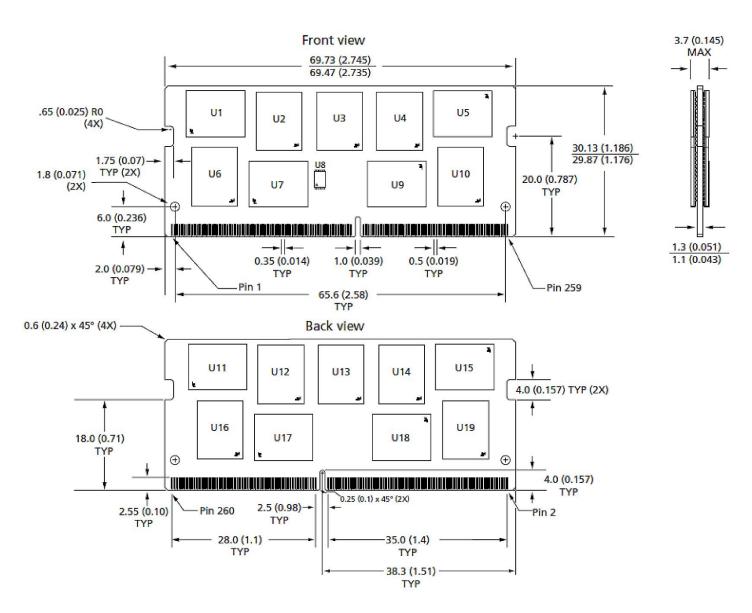


Speed Grade

Frequency	Data			C	AS Laten	cy Support				
Grade	Transfer Rate	CL11	CL12	CL13	CL14	CL15	CL16	CL17	CL19	CL-tRCD-tRP
DDR4-2666	PC4-21300	1600	1600	1866	1866	2133	2133	2400	2666	19-19-19

Package Dimensions

Unit: mm



Tolerances : + 0.15mm unless otherwise specified